

PROCESS AND APPARATUS FOR TREATING GAS CONTAINING  
FLUORINE-CONTAINING COMPOUNDS AND CO.

ABSTRACT OF THE DISCLOSURE

The purpose of the present invention is to provide a  
5 process and an apparatus for efficiently treating a gas  
containing fluorine-containing compounds and CO to be  
discharged, for example, from the step of dry cleaning the  
inner surfaces and the like of a semiconductor  
manufacturing apparatus or the step of etching various  
10 types of formed films such as oxide films in the  
semiconductor industry. In order to accomplish the above-  
mentioned purpose, the gas treating process according to  
the present invention is a process for treating a gas  
containing fluorine-containing compounds and CO which  
15 comprises contacting the above described gas with O<sub>2</sub> and  
H<sub>2</sub>O at a temperature of 850°C or higher to oxidize the CO  
to CO<sub>2</sub>; and then contacting the gas with γ-alumina at a  
temperature of 600 to 900°C to decompose the fluorine-  
containing compounds.